March 1991

DM74LS123 Dual Retriggerable One-Shot with Clear and Complementary Outputs

General Description

The DM74LS123 is a dual retriggerable monostable multivibrator capable of generating output pulses from a few nanoseconds to extremely long duration up to 100% duty cycle. Each device has three inputs permitting the choice of either leading edge or trailing edge triggering. Pin (A) is an active-low transition trigger input and pin (B) is an active-high transition trigger input. The clear (CLR) input terminates the output pulse at a predetermined time independent of the timing components. The clear input also serves as a trigger input when it is pulsed with a low level pulse transition (`LT'). To obtain the best trouble free operation from this device please read the operating rules as well as the NSC one-shot application notes carefully and observe recommendations.

Features

- DC triggered from active-high transition or active-low transition inputs
- Retriggerable to 100% duty cycle

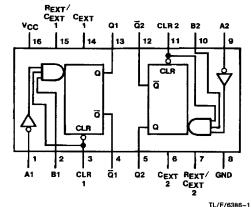
- Compensated for V_{CC} and temperature variations
- Triggerable from CLEAR input
- DTL, TTL compatible
- Input clamp diodes

Functional Description

The basic output pulse width is determined by selection of an external resistor ($R_{\rm X}$) and capacitor ($C_{\rm X}$). Once triggered, the basic pulse width may be extended by retriggering the gated active-low transition or active-high transition inputs or be reduced by use of the active-low or CLEAR input. Retriggering to 100% duty cycle is possible by application of an input pulse train whose cycle time is shorter than the output cycle time such that a continuous "HIGH" logic state is maintained at the "Q" output.

Connection Diagram

Dual-in-Line Package



Order Number DM74LS123M or DM74LS123N See NS Package Number M16A or N16E

Function Table

	nputs	Outputs			
CLEAR	A	В	Q	Q	
L	х	х	L	Н	
X	н	X	L	н	
X	x	L	L	H	
ј н	L	↑	九	7	
Н	↓	н	小	T	
1 ↑	L	н	л.	T	

- H = High Logic Level
- L = Low Logic Level
- X = Can Be Either Low or High
- Positive Going Transition
- L = Negative Going Transition
- ___ = A Positive Pulse
- □ = A Negative Pulse

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Absolute Maximum Ratings (Note)

If Military/Aerospace specified devices are required, please contact the National Semiconductor Sales Office/Distributors for availability and specifications.

Supply Voltage Input Voltage 7V

Operating Free Air Temperature Range 0°C to +70°C Storage Temperature -65°C to +150°C

Note: The "Absolute Maximum Ratings" are those values beyond which the safety of the device cannot be guaranteed. The device should not be operated at these limits. The parametric values defined in the "Electrical Characteristics" table are not guaranteed at the absolute maximum ratings. The "Recommended Operating Conditions" table will define the conditions for actual device operation.

Recommended Operating Conditions

Symbol	Parameter		Min	Nom	Max	Units
V _{CC}	Supply Voltage		4.75	5	5.25	V
VIH	High Level Input Voltage		2			V
V _{IL}	Low Level Input Voltage				0.8	٧
¹ он	High Level Output Current				-0.4	mA
loL	Low Level Output Current				8	mA
t₩	Pulse Width (Note 6)	A or B High	40			ns
		A or B Low	40			
		Clear Low	40			
R _{EXT}	External Timing Resistor		5		260	kΩ
C _{EXT}	External Timing Capacitance			No Restriction)	μF
C _{WIRE}	Wiring Capacitance at R _{EXT} /C _{EXT} Terminal				50	pF
TA	Free Air Operating Temperature		0		70	ô

Electrical Characteristics over recommended operating free air temperature range (unless otherwise noted)

Symbol	Parameter	Conditions	Min Typ (Note 1)		Max	Units
VI	Input Clamp Voltage	V _{CC} = Min, I _i = -18 mA			-1.5	V
V _{OH}	High Level Output Voitage	V _{CC} = Min, I _{OH} = Max V _{IL} = Max, V _{IH} = Min	2.7	3.4		٧
V _{OL}	Low Level Output Voltage	V _{CC} = Min, I _{OL} = Max V _{IL} = Max, V _{IH} = Min		0.35 0.5 _V	v	
		i _{OL} = 4 mA, V _{CC} = Min		0.25	0.4	
h	Input Current @ Max Input Voltage	V _{CC} = Max, V _I = 7V			0.1	mA
I _{tH}	High Level Input Current	V _{CC} = Max, V _I = 2.7V			20	μΑ
I _{IL}	Low Level Input Current	V _{CC} = Max, V _I = 0.4V			-0.4	mA
los	Short Circuit Output Current	V _{CC} = Max (Note 2)	-20		-100	mA
lcc	Supply Current	V _{CC} = Max (Notes 3,4 and 5)		12	20	mA

Note 1: All typicals are at $V_{CC} = 5V$, $T_A = 25$ °C.

Note 2: Not more than one output should be shorted at a time, and the duration should not exceed one second.

Note 3: Quiescent I_{CC} is measured (after clearing) with 2.4V applied to all clear and A inputs, B inputs grounded, all outputs open, C_{EXT} = 0.02 µF, and $R_{EXT} = 25 \, k\Omega$.

Note 4: I_{CC} is measured in the triggered state with 2.4V applied to all clear and B inputs, A inputs grounded, all outputs open, $C_{EXT}=0.02~\mu\text{F}$, and $R_{EXT}=25~k\Omega$.

Note 5: With all outputs open and 4.5V applied to all data and clear inputs, I_{CC} is measured after a momentary ground, then 4.5V is applied to the clock.

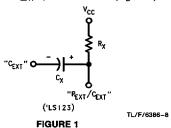
Note 6: $T_A = 25^{\circ}C$ and $V_{CC} = 5V$.

Symbol	Parameters	From (Input) To (Output)	$R_L = 2 k\Omega$				
			$C_L = 15pF$ $C_{EXT} = 0 pF, R_{EXT} = 5 k\Omega$		C _L = 15pF C _{EXT} = 1000 pF, R _{EXT} = 10 KΩ		Units
			Min	Max	Min	Max]
^t PLH	Propagation Delay Time Low to High Level Output	A to Q		33			ns
t _{PLH}	Propagation Delay Time Low to High Level Output	B to Q		44			ns
t _{PHL}	Propagation Delay Time High to Low Level Output	A to Q		45			ns
t _{PHL}	Propagation Delay Time High to Low Level Output	B to Q		56			ns
t _{PLH}	Propagation Delay Time Low to High Level Output	Clear to Q		45			ns
t _{PHL}	Propagation Delay Time High to Low Level Output	Clear to Q		27			ns
t _{WQ(Min)}	Minimum Width of Pulse at Output Q	A or B to Q		200			ns
t _{W(out)}	Output Pulse Width	A or B to Q			4	5	μs

Operating Rules

- 1. An external resistor (R_X) and an external capacitor (C_X) are required for proper operation. The value of C_X may vary from 0 to any necessary value. For small time constants high-grade mica, glass, polypropylene, polycarbonate, or polycstyrene material capacitors may be used. For large time constants use tantalum or special aluminum capacitors. If the timing capacitors have leakages approaching 100 nA or if stray capacitance from either terminal to ground is greater than 50 pF the timing equations may not represent the pulse width the device generates.
- 2. When an electrolytic capacitor is used for C_X a switching diode is often required for standard TTL one-shots to prevent high inverse leakage current. This switching diode is not needed for the 'LS123 one-shot and should not be used. In general the use of the switching diode is not recommended with retriggerable operation.

Furthermore, if a polarized timing capacitor is used on the 'LS123 the negative terminal of the capacitor should be connected to the "CEXT" pin of the device (Figure 1).



3. For $C_X >> 1000$ pF the output pulse width (T_W) is defined as follows:

$$T_W = KR_X C_X$$

where $[R_X \text{ is in } k\Omega]$
 $[C_X \text{ is in } pF]$
 $[T_W \text{ is in ns]}$
 $K \approx 0.37$

4. The multiplicative factor K is plotted as a function of C_{χ} below for design considerations:

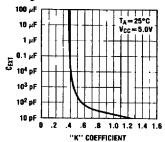
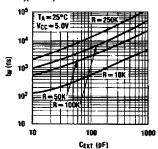


FIGURE 2

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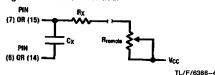
Operating Rules (Continued)

5. For $C_X <$ 1000 pF see Figure 3 for T_W vs C_X family curves with R_X as a parameter:



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To obtain variable pulse widths by remote trimming, the following circuit is recommended:



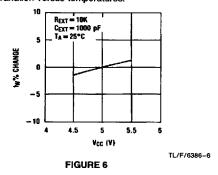
Note: "Rremote" should be as close to the device pin as possible.

7. The retriggerable pulse width is calculated as shown below: $T = T_W + t_{PLH} = K \times R_X \times C_X + t_{PLH}$

FIGURE 4

FIGURE 5

Output pulse width variation versus V_{CC} and temperatures: Figure 6 depicts the relationship between pulse width variation versus V_{CC}, and Figure 7 depicts pulse width variation versus temperatures.



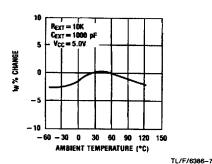


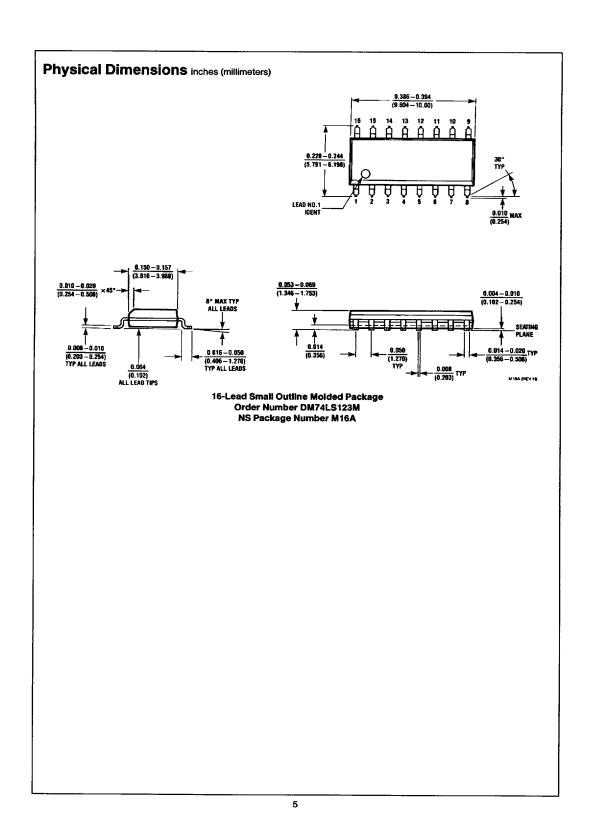
FIGURE 7

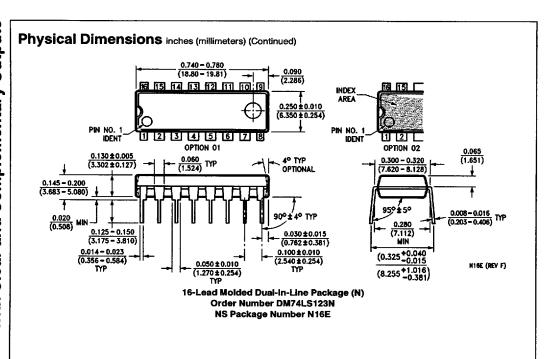
- 9. Under any operating condition C_X and R_X must be kept as close to the one-shot device pins as possible to minimize stray capacitance, to reduce noise pick-up, and to reduce I-R and Ldi/dt voltage developed along their connecting paths. If the lead length from C_X to pins (6) and (7) or pins (14) and (15) is greater than 3 cm, for example, the output pulse width might be quite different from values predicted from the appropriate equations. A non-inductive and low capacitive path is necessary to ensure complete discharge of C_X in each cycle of its operation so that the output pulse width will be accurate.
- The C_{EXT} pins of this device are internally connected to the internal ground. For optimum system performance they should be hard wired to the system's return ground plane.
- 11. V_{CC} and ground wiring should conform to good high-frequency standards and practices so that switching translents on the V_{CC} and ground return leads do not cause interaction between one-shots. A 0.01 μF to 0.10 μF bypass capacitor (disk ceramic or monolithic type) from V_{CC} to ground is necessary on each device. Furthermore, the bypass capacitor should be located as close to the V_{CC}-pin as space permits.

For further detailed device characteristics and output performance please refer to the NSC one-shot application note AN-372.

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